

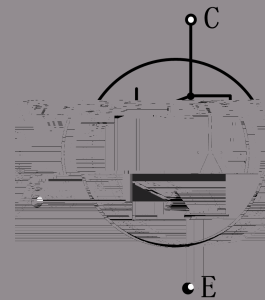
- $V_{CE} = 650V$
- $I_C = 10A @ V_{CE} = 100V$
- $V_{CE(sat)} = 1.8V$

TO-252



- High ruggedness performance
- 10 μ s short circuit capability
- Positive $V_{CE(sat)}$ temperature coefficient
- High efficiency for motor control
- Excellent current sharing in parallel operation
- RoHS compliant

- Home appliances
- Motor drives



Type	Marking	Package	Packaging method
JJT10N65ST	T1065ST	TO-252	Tape and reel



CES	Collector-emitter voltage	650	V
GES	Gate-emitter voltage	± 20	V
C	Continuous collector current ($I_{c=25}$)	20	A
	Continuous collector current ($I_{c=100}$)	10	A
CM	Pulsed collector current, I_p limited by v_{jmax}	40	A
F	Diode continuous forward current ($I_{c=100}$)	10	A
FM	Diode maximum current, I_p limited by v_{jmax}	40	A
sc	Short circuit withstand time	10	μs
tot	Power dissipation ($P_{c=25}$)	75	W
	Power dissipation ($P_{c=100}$) ! e 7		



CES	Collector-emitter breakdown voltage	$V_{GE}=0V, I_C=250\mu A$	650	-	-	V
CES	Collector-emitter leakage current	$V_{CE}=650V, V_{GE}=0V$	-	-	50	μA
	Gate leakage current, forward	$V_{GE}=20V, V_{CE}=0V$	-	-	100	nA
GES	Gate leakage current, reverse	$V_{GE}=-20V, V_{CE}=0V$	-	-	-100	nA
G						



($v_j=25$ unless otherwise specified)

F	Diode forward voltage	$I_F=10A$	-	1.4	-	V
		$I_F=10A, v_j=175$	-	1.2	-	V
t_{rr}	Diode reverse recovery time	$V_R=400V$ $I_F=10A$ $d I_F/d t = -750A/\mu s$	-	57	-	ns
I_{rrm}	Diode peak reverse recovery current		-	12	-	A
Q_{rr}	Diode reverse recovery charge		-	411	-	nC
t_{rr}	Diode reverse recovery time	$V_R=400V$ $I_F=10A$ $d I_F/d t = -750A/\mu s$ $v_j=175$	-	124	-	ns
I_{rrm}	Diode peak reverse recovery current		-	13	-	A
Q_{rr}	Diode reverse recovery charge		-	737	-	nC

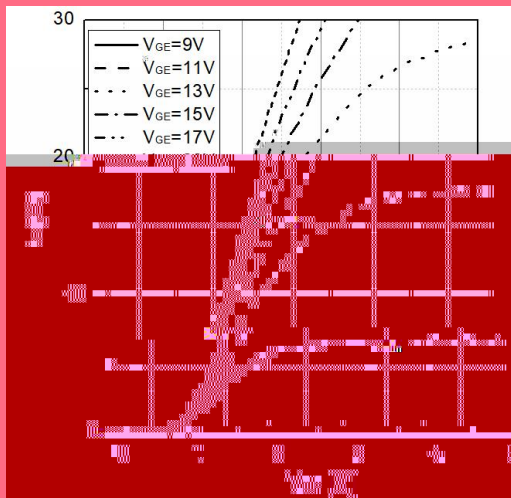


Fig 1. Typical output characteristic ($v_j=25$)

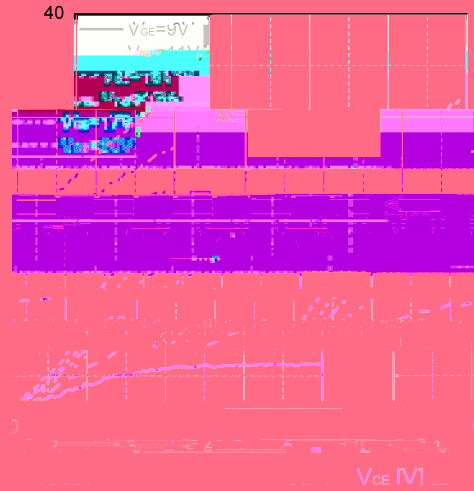


Fig 2. Typical output characteristic ($v_j=175$)

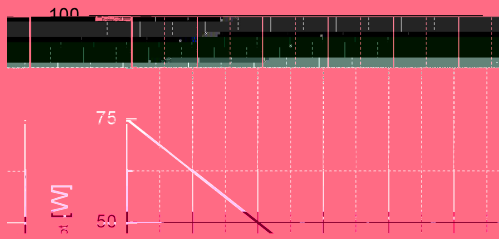


Fig 3. Power dissipation as a function of

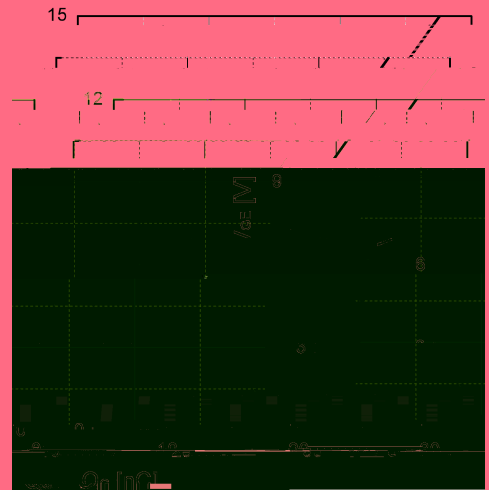


Fig 4. Typical Gate charge

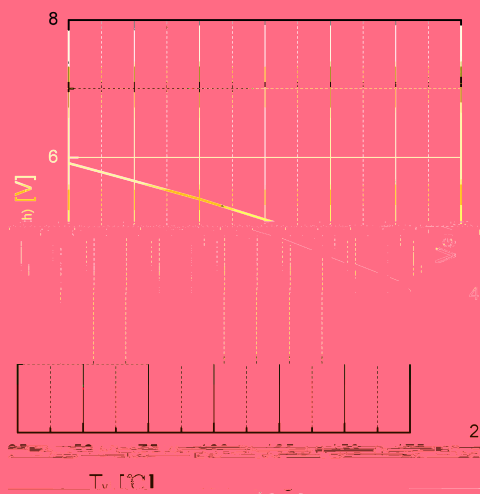


Fig 5. Typical $V_{GE(th)}$ as a function of v_j ($c=1mA$)

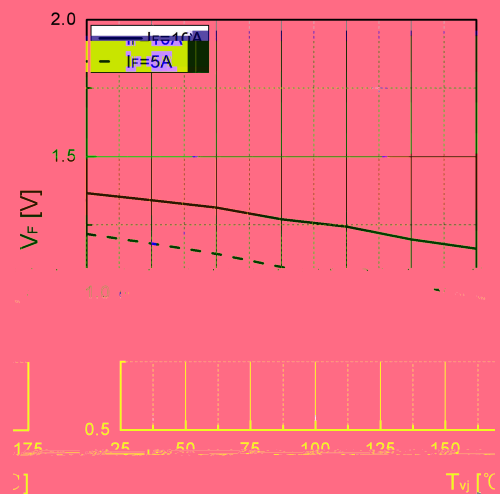


Fig 6. Typical V_F as a function of v_j

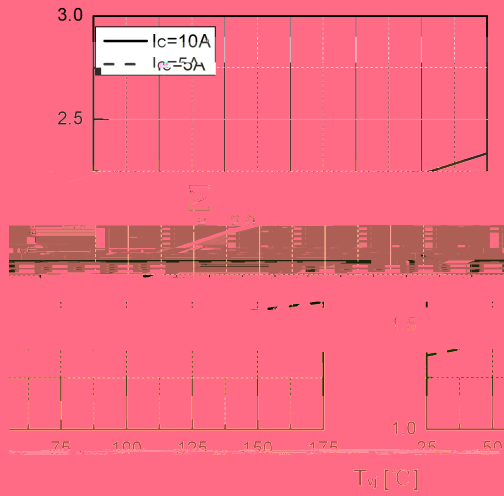


Fig 7. Typical C_{Esat} as a function of T_{vj}

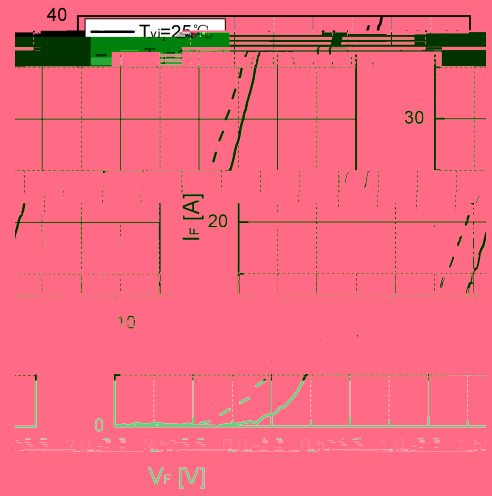


Fig 8. Typical I_F as a function of V_F

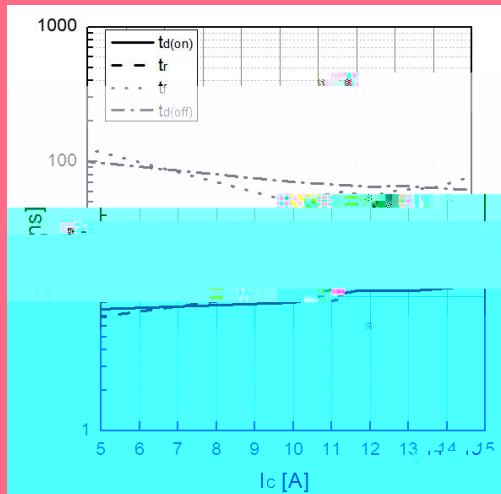


Fig 9. Typical switching time as a function of I_c

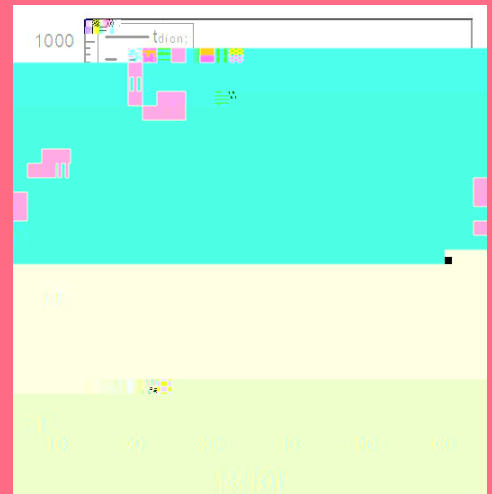


Fig 10. Typical switching times as a function of R_g

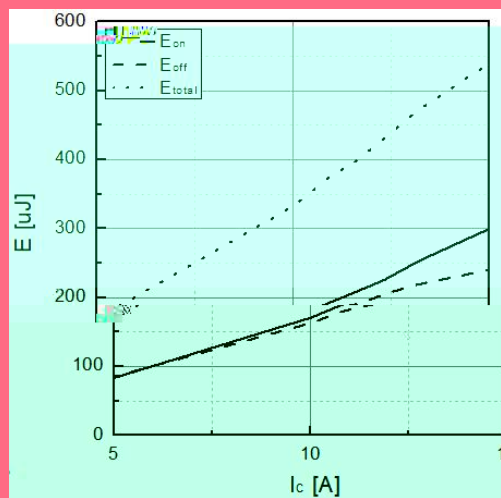


Fig 11. Typical switching energy losses as a function of I_c

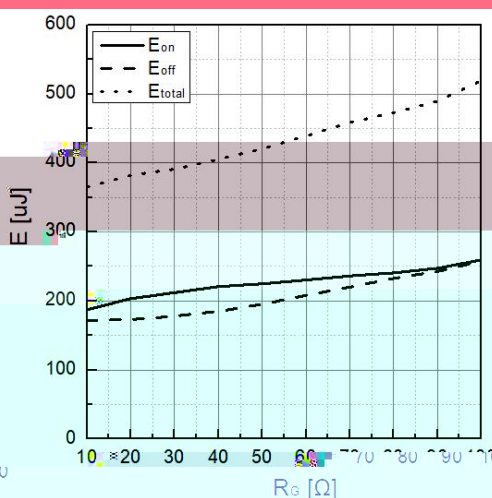
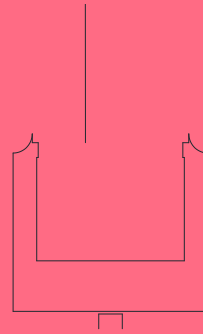
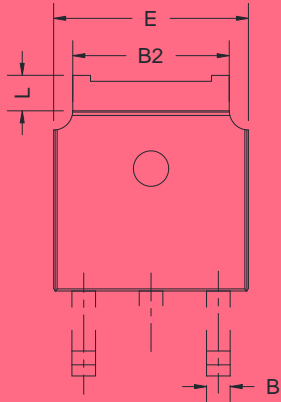


Fig 12. Typical switching energy losses as a function of R_g





Date	Revision	Changes
2023-12-23	1.0	Initial release
2025-02-06	Rev 1.1	Update
2025-04-08	Rev 1.2	Character Update